

Product brief

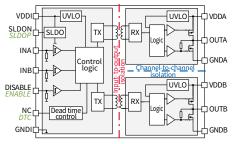
Dual-channel isolated EiceDRIVER™ family

Fast, robust, dual-channel, functional and reinforced isolated Si and SiC MOSFET gate driver ICs with accurate and stable timing

Overview

The dual-channel isolated EiceDRIVER[™] product family is designed for the use in high-performance power conversion applications. Very strong 4 A/8 A source/sink dualchannel gate drivers increase efficiency in CoolMOS[™], CoolSiC[™] and OptiMOS[™] MOSFET half-bridges. The low propagation delay of 37 ns, combined with highly accurate and stable timing overtemperature and production, enables further efficiency gains within and across galvanically isolated power stages or in multi-phase/multi-level topologies. The availability of functional and reinforced isolated drivers in different packages makes these a perfect fit for both primary side and (safe) secondary side control. Gate driver outputs come with a high 5 A reverse current capability and 150 V/ns CMTI robustness for high dv/dt power loops. For slower switching or driving smaller MOSFETs, 1 A/2 A peak current product variants are available as well.

Device overview



Product family overview

System benefits

Product key features

- Fast power switching with accurate timing
- $\,\,$ > Available with 4 A/8 A and 1 A/2 A source/sink currents
- Propagation delay typ. 37 ns with 3 ns
- channel-to-channel precision
- > Max. propagation delay variation ~14 ns

Optimized for area and system BOM

- Isolation and driver in one package
- > Low power dissipation due to low on-resistance
- Output stages with 5 A reverse current capability

Robustness against switching noise

- Floating drivers are able to handle large inductive voltage over- and undershoots
- Very good common mode transient immunity CMTI >150 V/ns
- > Undervoltage lockout function for switch protection
- Output- to -output channel isolation
- Functional level galvanic isolation

Input- to output channel isolation

> Functional and reinforced galvanic isolation

Product benefits

- Efficiency gain and lower losses
- > Lower switching losses in half-bridges due to fast and accurate turn on/off
- Perfect for new digital, fast high resolution PWM control including light load optimization
- Improved thermal behavior at smaller form factor
- $\scriptstyle \rightarrow$ LGA with 1 mm, DSO with 2.3 mm package height
- versus volume > 1 cm for pulse transformers
- Eliminates two costly protection diodes on the gate driver outputs

Protection and safe operation

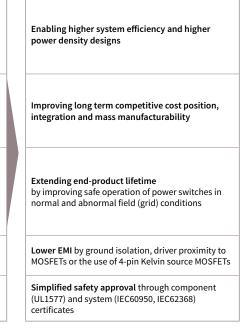
- Ideal for use in high power designs with fast switching transients
- Reliable CT coreless transformer PWM signal chain to turn on high side MOSFETs

Flexible configurations

> HS+LS, HS+HS, LS+LS or 2x Imax on 1xHS

Regulatory safety

- > Functional for primary-side control
- > Reinforced for secondary-side control

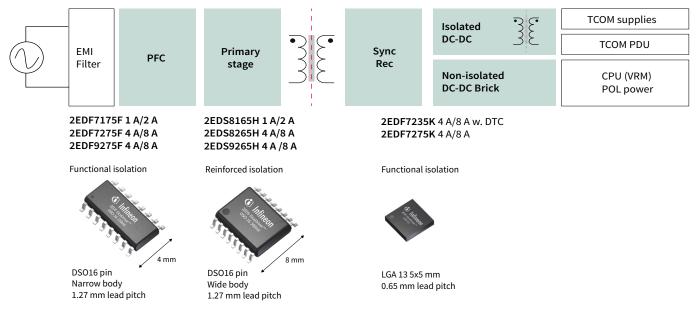




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System application diagram



Product portfolio

Part number	Orderable part number (OPN)	Package	Input type	Driver source/ sink current	Gate driver UVLO	Input to output isolation				Dead-
						Isolation class	Rating	Surge testing	Safety certification	time control
2EDF7175F	2EDF7175FXUMA1	NB-DSO16 10 x 6 mm	Dual-mode (IN_A, IN_B)	1 A/2 A	414		V _{IO} = 1.5 kV _{DC}	n.a.	n.a.	no
2EDF7275F	2EDF7275FXUMA1			4 A/8 A	4 V	Functional				
2EDF9275F	2EDF9275FXUMA1				13 V					
2EDS8165H	2EDS8165HXUMA1	WB-DSO16 10.3 x 10.3 mm		1 A/2 A	<u></u>	Reinforced	V _{IOTM} = 8 kV _{peak} V _{ISO} = 5.7 kV _{rms} (UL1577)	VIOCM - IUKV posk	UL1577 IEC60950 IEC62368 CQC	
2EDS8265H	2EDS8265HXUMA1			4 A/8 A	8 V					
2EDS9265H	2EDS9265HXUMA1				13 V					
2EDF7235K	2EDF7235KXUMA1	LGA13 5.0 x 5.0 mm			4 V	Functional	V _{IO} = 1.5 kV _{DC}	n.a.	n.a.	yes
2EDF7275K	2EDF7275KXUMA1									no

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